

Role of molybdenum ions in lead zinc phosphate glass system by means of dielectric studies

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PbO-ZnF₂-P₂O₅ glasses doped with different mol% (0.1 to 1.0) of MoO₃ have been prepared. Dielectric properties $\epsilon'(\omega)$, $\tan\delta$, σ_{AC} , of the synthesized samples were calculated from frequency measurements versus temperature. Space charge polarization was used to analyze the temperature and frequency dispersions of dielectric constant $\epsilon'(\omega)$ and dielectric loss $\tan\delta$. Quantum mechanical tunneling model was employed to explain the origin of AC conductivity. The AC conductivity exhibited an increasing trend with increasing concentration of MoO₃ (up to 0.2 mol%) but the activation energy for conduction decreased. The plots of AC conductivity revealed that the relaxation dynamics depends on MoO₃ dopant concentration.

Keywords: *electrical and dielectric properties; quantum mechanical tunneling; AC conductivity; relaxation dynamics*

1. Introduction

In recent years, the study of electrical properties, including dielectric characteristics in glasses plays a significant role in solid state electronic devices [1]. The main applications of glassy dielectrics involve capacitance elements in electronic circuits and electrical insulators. Transition metal ions (TMI) in glasses are beneficial in electrochromic devices, such as smart windows and flat panel displays [2–7]. A small percentage concentration of TMI in oxide glasses resulted in their semiconducting properties [8, 9] and for these glasses the dielectric relaxation effect was due to electron hopping pairs [10].

Phosphate glasses exhibit distinctive physical properties when compared to the other borate and silicate glasses. The phosphate glasses have lower coefficient of thermal expansion, high ultraviolet transmission and comparatively lower melting temperature [11–13]. The semiconductor oxide MoO₃ acts as a conditional glass former as well as a modifier. When phosphate glasses are mixed with this oxide, their physical properties and chemical durability are expected to be improved [14, 15]. The MoO₃ mixed glasses find potential applications in developing alphanumeric displays, microbatteries, gas sensors, and memory devices [16, 17]. The stable oxidation states, Mo⁵⁺ and Mo⁶⁺ of MoO₃, are anticipated to change the dielectric properties depending on the composition of glass.

PbO-P₂O₅ glasses are recognized for their stability and moisture resistance. PbO plays a dual

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role: a modifier for Pb–O ionic bond and a glass former for Pb–O covalent bond [18–20]. The addition of ZnF_2 to this type of glass system increases liquidus temperature and corrosion resistance of the glasses [21]. Zn^{2+} cation is responsible for the good glass forming ability.

2. Experimental

Lead zinc phosphate glasses of the composition $(20 - x)\text{PbO}-30\text{ZnF}_2-50\text{P}_2\text{O}_5:x\text{MoO}_3$, with $x = 0.1, 0.2, 0.3, 0.4, 0.8$ and 1.0 mol% (labeled as M_1, M_2, M_3, M_4, M_8 and M_{10}) were prepared by the melt quenching method [22, 23]. The chemicals (from Acros Co.) $\text{PbO} \geq 99\%$, $\text{ZnF}_2 \geq 99.8\%$, $\text{P}_2\text{O}_5 \geq 99\%$ and $\text{MoO}_3 \geq 99\%$ were weighed and the mixture of the compounds was melted in a platinum crucible in a PID electric furnace at a temperature of 1273 K for one hour. The bubble free liquid melt was transferred into a pre-heated brass mould and the samples were annealed at 523 K for five hours. The density of the prepared glass samples was measured by the Archimedes principle with distilled water as a buoyant liquid. The actual compositions of the glass samples and other physical parameters such as average molecular weight, ion concentration, mean ion separation distance and polaron radius have been evaluated and tabulated in Table 1.

X-ray diffraction study confirmed the amorphous nature of the prepared glass samples. SEIFERT diffractometer model SO-DEBYE FLUX 202 was used for X-ray diffraction analysis of the prepared samples. Silver coating on both sides of the sample acted as electrodes for measurement of dielectric properties [24, 25]. The dielectric measurements of the samples in the present investigation were performed with HP 4263B LCR Meter in the frequency range of 10^2 Hz to 10^5 Hz and the temperature range of 30 °C to 350 °C. Radart Q-Meter was used for high frequency measurements.

3. Results

Fig. 1 shows the frequency variation of dielectric constant ϵ' and loss $\tan\delta$

of the $\text{PbO}-\text{ZnF}_2-\text{P}_2\text{O}_5:\text{MoO}_3$ glasses. At room temperature and at high frequency of 100 kHz the values of ϵ' and $\tan\delta$ were found as 9.3 and 0.0074, respectively, for the pure sample M_0 . These values have increased with increasing concentration of MoO_3 up to 0.2 mol% (inset of Fig. 1) further, larger dielectric constant values were noted at the low frequency 1 kHz.

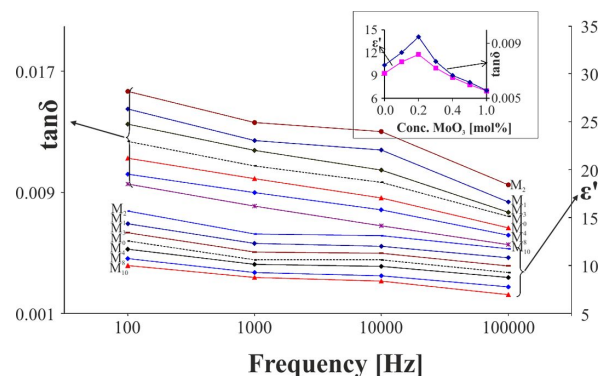


Fig. 1. Variation of dielectric constant and loss tangent with frequency at room temperature for $\text{PbO}-\text{ZnF}_2-\text{P}_2\text{O}_5:\text{MoO}_3$ glasses. The inset figure represents the variation of ϵ' and $\tan\delta$ with the concentration of MoO_3 at 100 kHz.

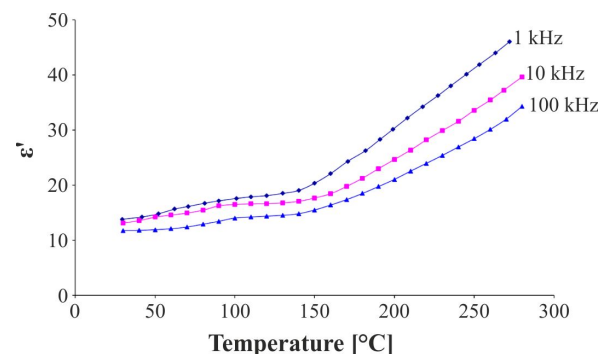


Fig. 2. Variation of dielectric constant of glass M_2 with temperature at different frequencies.

Fig. 2 presents the variation of dielectric constant with temperature at different frequencies for the glass sample M_2 . The measured ϵ' values of the sample were found to increase with temperature and the rate of the increase was larger at low frequencies; the other samples also followed the same trend.

Table 1. Data on various physical properties of PbO-ZnF₂-P₂O₅:MoO₃ glasses.

Sample	Glass composition	Density [g/cm ³]	Average molecular weight	Concentration of molybdenum ions N _i [$\times 10^{21}$ ions per cm ³]	Interionic distance r _i [Å]	Polaron radius r _p [Å]
M ₀	20.0 PbO-30ZnF ₂ -50P ₂ O ₅	2.7018	116.4	—	—	—
M ₁	19.9PbO-30ZnF ₂ -50 P ₂ O ₅ :0.1MoO ₃	2.7047	116.5	1.65	7.78	2.95
M ₂	19.8PbO-30ZnF ₂ -50P ₂ O ₅ :0.2MoO ₃	2.7099	116.6	2.79	7.09	2.86
M ₃	19.7PbO-30ZnF ₂ -50P ₂ O ₅ :0.3MoO ₃	2.7105	116.7	4.19	6.20	2.50
M ₄	19.6PbO-30ZnF ₂ -50P ₂ O ₅ :0.4MoO ₃	2.7176	116.8	5.66	5.63	2.27
M ₈	19.2PbO-30ZnF ₂ -50P ₂ O ₅ :0.8MoO ₃	2.7870	117.2	11.458	4.44	1.79
M ₁₀	19.0PbO-30ZnF ₂ -50P ₂ O ₅ :1.0MoO ₃	2.8210	117.4	12.356	4.33	1.74

Fig. 3 depicts a comparison of dielectric constant variation with temperature for PbO-ZnF₂-P₂O₅:MoO₃ glasses measured at 1 kHz. The temperature dependent dielectric constant ϵ' is the highest for sample M₂. The variation of dielectric loss ($\tan\delta$) with temperature at different frequencies for sample M₄ and comparison of $\tan\delta$ variation with temperature for PbO-ZnF₂-P₂O₅:MoO₃ glasses have been shown in Fig. 4 and Fig. 5, respectively. The relaxation peak and $\tan\delta$ values are found to increase with the MoO₃ up to 0.2 mol%. The activation energy AE of the samples has been calculated from equation 1 and tabulated in Table 2. The activation energy of 2.51 eV is the lowest for sample M₂:

$$f = f_0 e^{-W_d/KT} \quad (1)$$

where W_d is the activation energy, f is resonance frequency, f_0 is a constant, K is the Boltzmann constant and T is temperature.

The AC conductivity of the samples was evaluated from the equation:

$$\sigma_{AC} = \omega \epsilon' \epsilon_0 \tan\delta \quad (2)$$

The plots of σ_{AC} versus $1/T$ (evaluated at 100 kHz) for PbO-ZnF₂-P₂O₅:MoO₃ glasses are shown in Fig. 6. The activation energy for conduction in the high temperature region was evaluated from these plots, and collected in Table 2. Fig. 7 presents the isotherms (drawn at 200 °C, 220 °C and 240 °C) of σ_{AC} for PbO-ZnF₂-P₂O₅:MoO₃ glasses at 10 kHz. Fig. 8 shows the X-ray diffraction patterns of the prepared glasses and does not

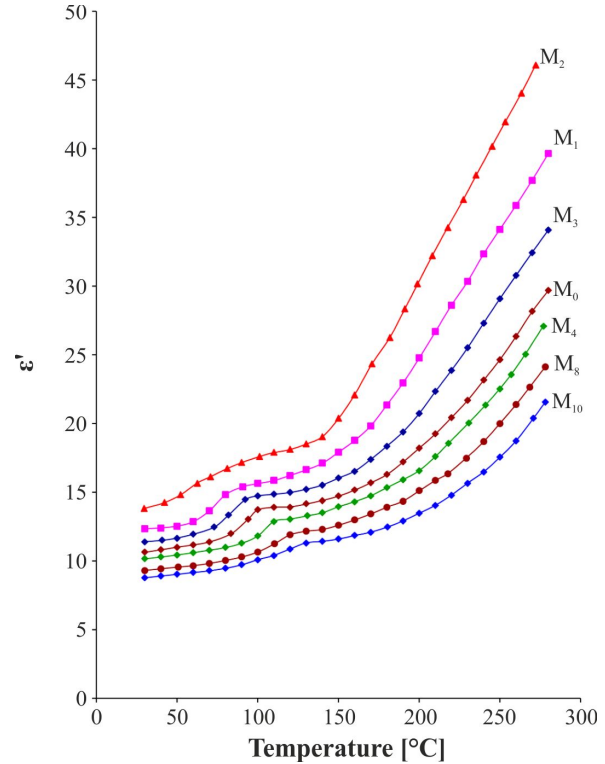


Fig. 3. A comparison of variation of dielectric constant with temperature measured at 1 kHz for PbO-ZnF₂-P₂O₅:MoO₃ glasses.

indicate any line of diffraction which confirms the amorphous nature of the glass samples.

4. Discussion

Molybdenum, belonging to the intermediate class of glass forming ions, was found to exist in two ionic states, i.e. Mo⁵⁺ and Mo⁶⁺.

Table 2. Dielectric properties of PbO-ZnF₂-P₂O₅:MoO₃ glasses.

Sample	Temp [°C]	Dielectric constant			Dielectric loss			AE for dipoles [eV]
		1 kHz	10 kHz	100 kHz	1 kHz	10 kHz	100 kHz	
M ₀	30	10.62	10.61	09.30	0.011	0.010	0.007	2.95
	100	13.72	12.29	10.38	0.020	0.012	0.009	
	250	24.64	22.68	19.64	0.103	0.087	0.070	
M ₁	30	12.33	12.20	10.80	0.012	0.011	0.009	2.65
	100	15.62	14.90	13.11	0.016	0.015	0.018	
	250	34.12	30.46	26.50	0.219	0.210	0.180	
M ₂	30	13.28	13.12	11.76	0.014	0.013	0.010	2.51
	100	17.59	16.50	14.04	0.174	0.017	0.016	
	250	40.18	33.61	28.46	0.402	0.397	0.329	
M ₃	30	11.40	11.28	09.98	0.011	0.011	0.008	2.58
	100	14.73	13.85	11.58	0.014	0.020	0.011	
	250	29.08	26.76	23.31	0.103	0.087	0.070	
M ₄	30	10.15	09.94	08.76	0.011	0.008	0.006	3.10
	100	11.82	10.89	09.51	0.013	0.009	0.007	
	250	22.53	20.16	16.67	0.069	0.055	0.047	
M ₈	30	09.30	08.96	07.77	0.009	0.008	0.006	3.25
	100	10.65	09.69	08.35	0.010	0.009	0.007	
	250	20.00	17.68	14.09	0.050	0.034	0.032	
M ₁₀	30	08.77	08.37	06.96	0.008	0.006	0.005	3.42
	100	10.09	08.93	09.27	0.009	0.007	0.006	
	250	17.54	14.77	11.90	0.036	0.023	0.021	

Table 3. AC conductivity of PbO-ZnF₂-P₂O₅:MoO₃ glasses.

Sample	Austin N(E _f) [10 ²¹ eV ⁻¹ /cm ³]	Butcher N(E _f) [10 ²¹ eV ⁻¹ /cm ³]	Pollak N(E _f) [10 ²¹ eV ⁻¹ /cm ³]	AE for conduction [eV]
M ₀	1.318	0.555	1.339	0.356
M ₁	1.530	0.638	1.555	0.332
M ₂	1.712	0.714	1.739	0.311
M ₃	1.414	0.590	1.437	0.343
M ₄	1.228	0.512	1.248	0.408
M ₈	1.099	0.459	1.117	0.445
M ₁₀	1.027	0.428	1.043	0.489

The structure of phosphate network significantly depends on its oxidation state and position it occupies. Mo⁵⁺ ions acting as modifier disrupt the phosphate glass network leading to dangling bonds with non-bridging oxygens (NBO), similar to divalent zinc ions [26–31]. The defected dangling bonds cause the relocation of charge carriers, increase the space

charge polarization and facilitate the enhancement of dielectric values ϵ' , $\tan\delta$ and σ_{AC} , of PbO-ZnF₂-P₂O₅:MoO₃ glasses up to 0.2 mol% of the dopant.

The measured decrease in dielectric values of the glasses beyond 0.2 mol% suggests a decrease in the concentration of free charge carriers [32, 33].

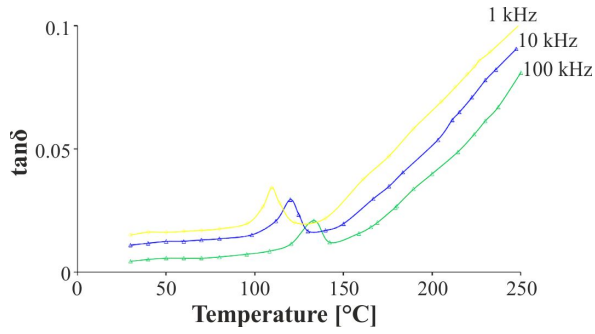


Fig. 4. Variation of dielectric loss with temperature measured at different frequencies for PbO-ZnF₂-P₂O₅ glasses doped with 0.4 mol% of MoO₃.

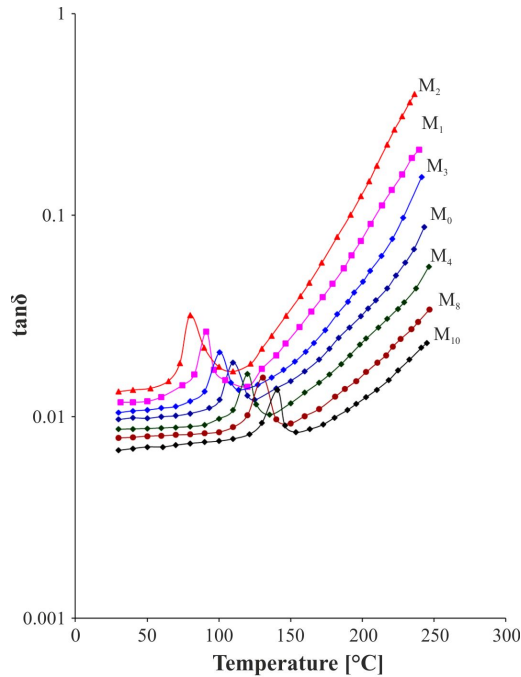


Fig. 5. A comparison of variation of dielectric loss with temperature for PbO-ZnF₂-P₂O₅:MoO₃ glasses measured at 10 kHz.

In other words, the fraction of Mo⁵⁺ ions in such glass samples is relatively low, hence, there is a reduction in the rate of increase of dielectric constant. The plots of variation of tanδ with the temperature for PbO-ZnF₂-P₂O₅:MoO₃ glasses exhibit dipolar relaxation effects due to Mo⁵⁺ ions state in Mo(V)O₃³⁻ [34, 35]. In the present glass system, beyond 0.2 mol% of MoO₃, we have

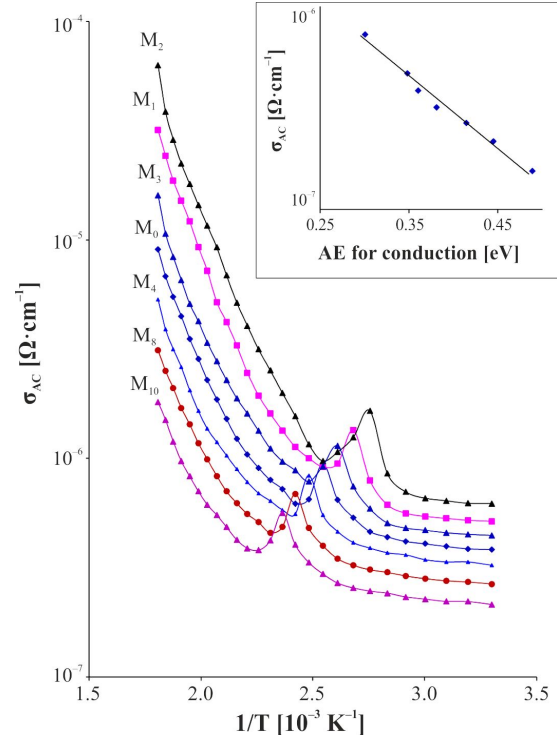


Fig. 6. Variation of AC conductivity with 1/T measured at 100 kHz for PbO-ZnF₂-P₂O₅ glasses doped with different concentrations of MoO₃.

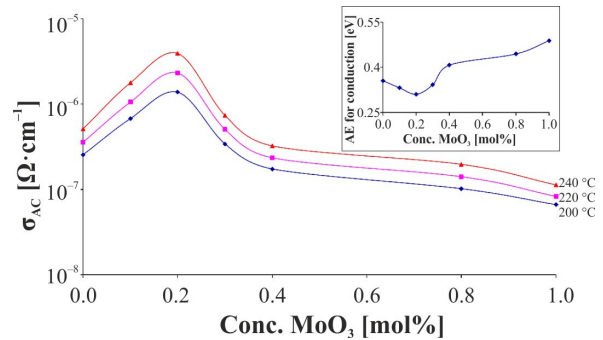


Fig. 7. Variation of AC conductivity with the concentration of MoO₃ measured at different temperatures and at a frequency of 10 kHz for PbO-ZnF₂-P₂O₅ glasses. The inset presents the variation of activation energy for conduction with the concentration of MoO₃.

observed a decrease in the intensity of the relaxation peaks and increasing trend of activation energy for dipoles. This observation confirms the existence of Mo⁶⁺ ions that participate in the glass network forming

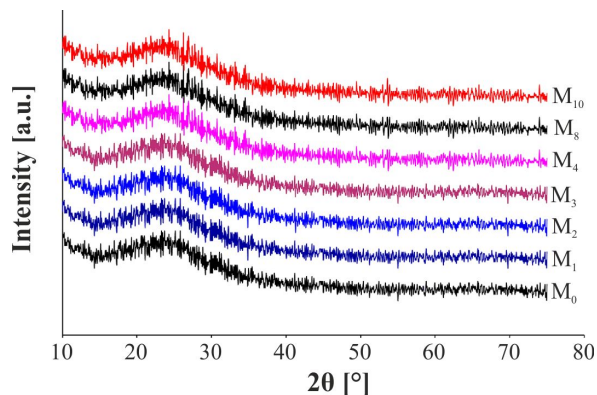


Fig. 8. XRD patterns of PbO-ZnF₂-P₂O₅:MoO₃ glasses.

for the samples from M₃ to M₁₀. A linear relationship between σ_{AC} and AE for conduction (inset of Fig. 6), suggests that the development of conductivity is directly related to the thermally stimulated mobility of the charge carriers [36]. Fig. 6 shows that σ_{AC} is maximum and AE for conduction (in the inset of Fig. 7) is minimum for sample M₂ due to transition from ionic (up to 0.2 mol%) to electronic conductivity (beyond 0.2 mol%) [37].

The active centers for the ionic conduction are due to the gradual increase of the content of modifier Mo⁵⁺ ions and either mobile electrons or polarons by the transition of Mo⁵⁺ to Mo⁶⁺. Quantum mechanical tunneling (QMT) model was adapted to explain the AC conductivity of the present glass system at low temperatures. According to QMT, equation for AC conductivity is:

$$\sigma(\omega) = \eta e^2 K_B T [NE_F]^2 \alpha^{-5} \omega \left[\ln \frac{\nu_{ph}}{\omega} \right]^4 \quad (3)$$

where NE_F is density of the defect energy states at the Fermi level, α is a decay constant ($\sim 0.485 \text{ \AA}^{-1}$), e is a charge of electron, K_B is the Boltzmann constant, ω is an angular frequency, ν_{ph} is phonon frequency ($5 \times 10^{12} \text{ Hz}$), T is temperature, η is a constant and its value is given by $\eta = \pi/3$ (Austin *et al.* [38]), $= 3.66\pi^2/6$ (Butcher *et al.* [39]), $= \pi^4/96$ (Pollak [40]).

The value of NE_F is observed to be maximal for the glasses mixed with 0.2 mol% of MoO₃

and beyond this range it is found to decrease (Table 3). Such variations are consistent with our prediction that in the glass M₂ there is a predominant existence of molybdenum Mo⁵⁺ states that act as modifier, whereas in the samples M₃ to M₁₀ the fraction of molybdenum is in Mo⁶⁺ states and these molybdenum ions participate in the glass network forming with MoO₄ structural units.

5. Conclusions

PbO-ZnF₂-P₂O₅:MoO₃ glasses (0 mol% to 1.0 mol%) were synthesized. Dielectric parameters ϵ' , $\tan\delta$, and σ_{AC} , were measured over a wide range of frequency at low temperature. It has been stated that the space charge polarization plays a vital role in the ϵ' and $\tan\delta$ of prepared glasses. We have observed an increase in the dielectric constant ϵ' , dielectric loss $\tan\delta$ and AC conductivity σ_{AC} up to 0.2 mol% of MoO₃, suggesting that a major portion of molybdenum ions got reduced to Mo⁵⁺ state. These ions acted as modifiers, which produced disorder in the glass network and enabled an increase of dielectric constant by contributing to the space charge polarization. The overall analysis indicated that glasses containing up to 0.2 mol% of MoO₃ are more appropriate for attaining good electrical conductivity.

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